

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N6263

SILICON LOW CURRENT
SCHOTTKY BARRIER DIODE

JEDEC D0-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N6263 is a Silicon Schottky Barrier Diode designed for low current, fast switching applications. This series is an ideal candidate to replace germanium switching diodes and conventional silicon switching diodes where ultra fast switching speeds and very low forward voltage drops are required. For higher breakdown voltages contact the factory for information on the CDSH-L Series.

MAXIMUM RATINGS($T_A=25^{\circ}\text{C}$)

	<u>SYMBOL</u>		<u>UNIT</u>
Peak Inverse Voltage	PIV	60	V
Average Forward Rectified Current	I_O	15	mA
Power Dissipation	P_D	400	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 TO +200	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_A=25^{\circ}\text{C}$)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNIT</u>
I_R	$V_R=50\text{V}$		200	nA
BV_R	$I_R=10\mu\text{A}$	60		V
V_F	$I_F=1.0\text{mA}$		0.410	V
V_F	$I_F=15\text{mA}$		1.0	V
C	$V_R=0, f=1.0\text{MHz}$		2.2	pF